

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of	)	
	)	
Shibly S. AHMED et al.	)	Group Art Unit: Unassigned
	)	
Application No.: Unassigned	)	Examiner: Unassigned
Divisional Application of 10/290,158	)	
	)	
Filed: June 24, 2003	)	
	)	
Title: DOUBLE GATE SEMICONDUCTOR	)	
DEVICE HAVING SEPARATE GATES	)	

**INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)**

U.S. Patent and Trademark Office  
2011 South Clark Place  
Customer Window  
Crystal Plaza Two, Lobby, Room 1B03  
Arlington, Virginia 22202

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97(b), Applicant(s) bring to the attention of the Examiner the documents listed on the attached PTO 1449. This Information Disclosure Statement (IDS) is being filed before the mailing date of a first Office Action in the above-referenced application. As such, no certification or fee is required. Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not attached, because such documents were properly submitted in an IDS in the parent application, application no.10/290,158, filed November 8, 2002.

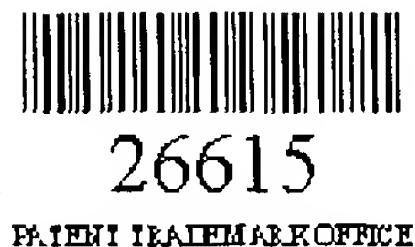
Applicant(s) respectfully request(s) that the Examiner consider the listed documents and indicate that they were considered by making appropriate notations on the attached form.

If any copending application(s) is/are cited on the attached PTO 1449, the Examiner's attention is directed to the foregoing application(s) in compliance with § 2001.06(b) of the Manual of Patent Examining Procedure. By identifying the copending application(s), the assignee and/or applicant of the application(s) do not waive confidentiality of the application(s). Accordingly, the U.S. Patent and Trademark Office is requested to maintain the confidentiality of the copending application(s) under 35 U.S.C. § 122.

This submission does not represent that a search has been made and does not constitute an admission that each or all of the listed documents are material or constitute "prior art." If the Examiner applies any of the documents as prior art against any claim in the application and Applicant(s) determine(s) that the cited document(s) do not constitute "prior art" under United States law, Applicant(s) reserve(s) the right to present to the Office the relevant facts and law regarding the appropriate status of such documents.

Applicant(s) further reserve(s) the right to take appropriate action to establish the patentability of the disclosed invention over the listed documents, should one or more of the documents be applied against the claims of the present application.

If there is any fee due in connection with the filing of this Statement, please charge the fee to our Deposit Account No. 50-1070.



Respectfully submitted,

HARRITY & SNYDER, L.L.P.


By:

A handwritten signature of Alan Pedersen-Giles is written over a horizontal line.

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Date: June 24, 2003

<b>INFORMATION DISCLOSURE CITATION</b> PTO-1449		 <b>26615</b> <small>PATENT TRADEMARK OFFICE</small>		ATTORNEY'S DKT No. H1105D		APPLICATION No. Unassigned	
				APPLICANT(S) Shilby S. AHMED et al.			
				FILING DATE June 24, 2003		GROUP Unassigned	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes      No	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.						
	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.						
	Xuejue Huang et al., "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.						
	Xuejue Huang et al., "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 67-70.						
	Yang-Kyu Choi et al., "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27.						
	U.S. Application Serial No. 10/290,330, filed November 8, 2002, entitled "DOUBLE-GATE SEMICONDUCTOR DEVICE," Bin Yu et al., 20 page specification, 11 sheets of drawings.						
	U.S. Application Serial No. 10/348,758, filed January 23, 2003, entitled "GERMANIUM MOSFET DEVICES AND METHODS FOR MAKING SAME," Judy Xilin An et al., 22 page specification, 29 sheets of drawings.						
EXAMINER				DATE CONSIDERED			

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).